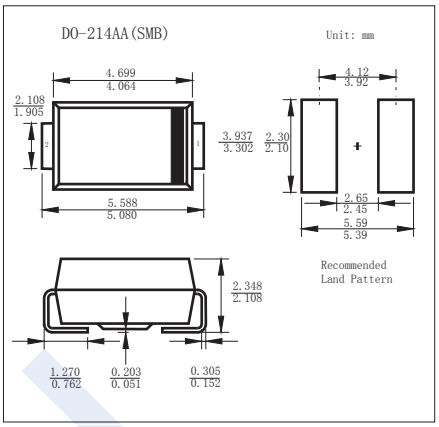
Ultrafast Rectifier Diodes

MURS260 (KURS260)

■ Features

- Glass passivated chip junction
- Ultrafast reverse recovery time
- Low switching losses, high efficiency
- High forward surge capability



■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Reverse Voltage	V_{RM}	600	V
Average Forward Current @ T_L=125℃	I_{FAV}	2	A
Peak Forward Surge Current @ 8.3 ms single half sine-wave superimposed on rated load	I_{FSM}	35	
Thermal Resistance Junction to Lead	$R_{\theta JL}$	15	℃/W
Junction Temperature	T_J	175	℃
Storage Temperature range	T_{stg}	-65 to 175	

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward voltage	V_F	I_F= 2 A,T_J=25℃			1.45	V
		I_F= 2 A,T_J=125℃			1.2	
Reverse voltage leakage current	I_R	T_J=25℃			5	uA
		T_J=125℃			150	
Reverse recovery time	t_{rr}	I_F=0.5A,I_R=1A,Irr=0.25A			50	ns
Reverse recovery time	t_{rr}	I_F=1A,di/dt=50A/us,V_R=30V,Irr=10％I_{RM}			75	
Reverse recovery time	t_{rr}	I_F=1A,di/dt=100A/us,recovery to 1V			50	

■ Marking

Marking	M2J

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■ Typical Characterisitics

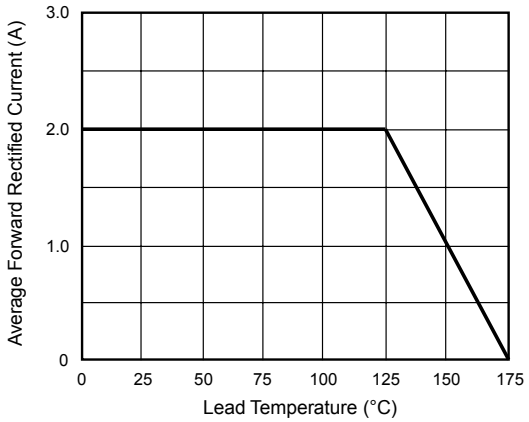

Figure 1. Forward Current Derating Curve

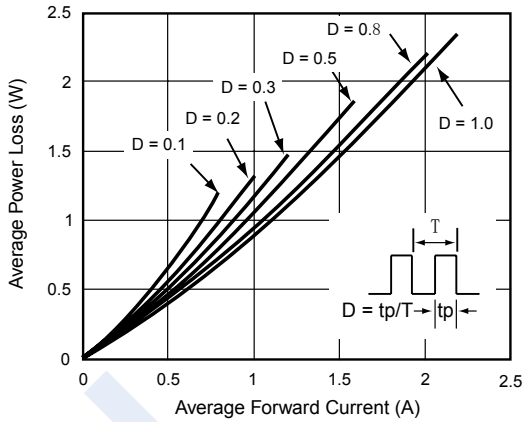

Figure 2. Forward Power Loss Characteristics

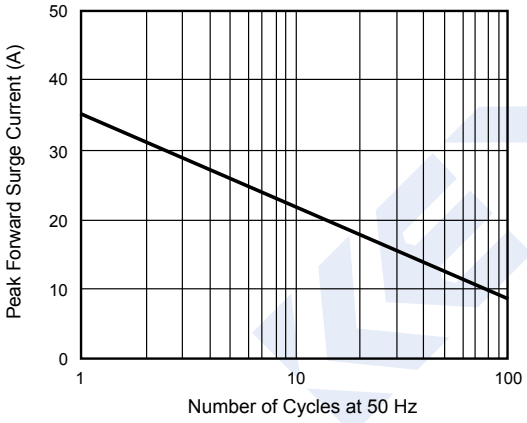

Figure 3. Maximum Non-Repetitive Peak Forward Surge Current

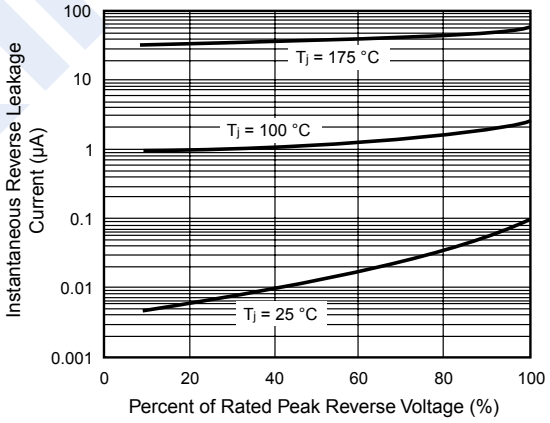

Figure 5. Typical Reverse Leakage Characteristics

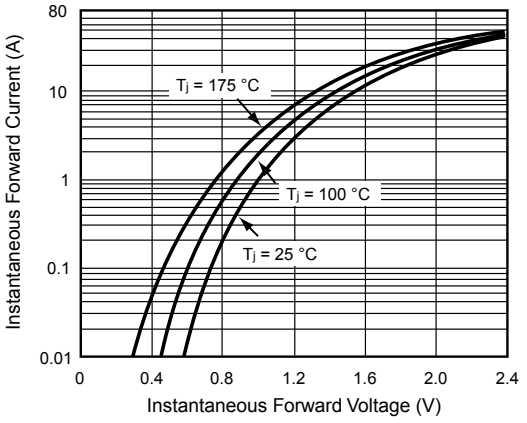

Figure 4. Typical Instantaneous Forward Characteristics

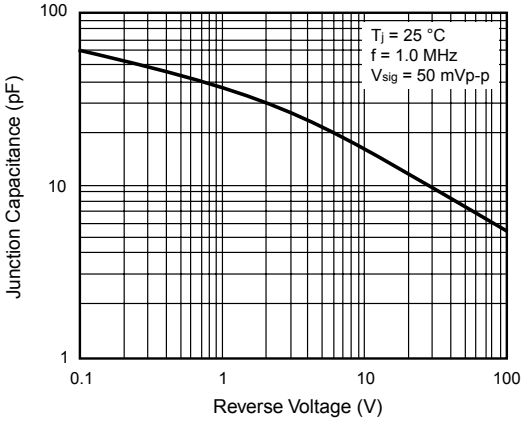

Figure 6. Typical Junction Capacitance